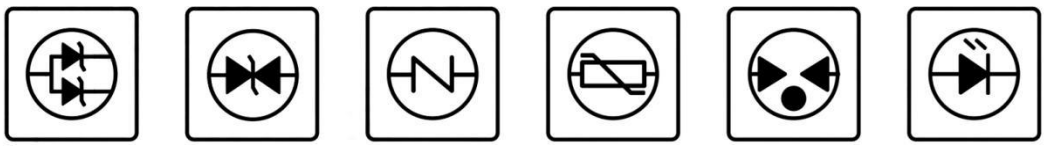
MSKSEMI
SEMICONDUCTOR



Product data sheet

SMAF

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

FEATURES

- Metal silicon junction,majority carrier conducion
- For surface mounted applications
- Low power loss,high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- Case:SMAF
- Terminals:Solderableper MIL-STD-750,Method 2026
- Approx.Weight:27mg 0.00086oz

Absolute Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.Single phase, half wave, 60Hz resistive or inductive load, for capacitive load, derate by 20 %

Parameter	Symbols	SS22F	SS24F	SS26F	SS28F	SS210F	SS212F	SS215F	SS220F	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	20	40	60	80	100	120	150	200	V
Maximum RMS voltage	V_{RMS}	14	28	42	56	70	84	105	140	V
Maximum DC Blocking Voltage	V_{DC}	20	40	60	80	100	120	150	200	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	2.0								A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	50				40				A
Max Instantaneous Forward Voltage at 2 A	V_F	0.55		0.70		0.85		0.95		V
Maximum DC Reverse Current T_a = 25° C at Rated DC Reverse Voltage T_a =100° C	I_R	0.5 10			0.3 5					mA
Typical Junction Capacitance 1)	C_j	220		80						pF
Operating Junction Temperature Range	T_j	-55 ~ +125								° C
Storage Temperature Range	T_{stg}	-55 ~ +150								° C

1) Measured at 1MHz and applied reverse voltage of 4 V D.C.

RATINGS AND CHARACTERISTIC CURVES SS22F THRU SS2200F

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

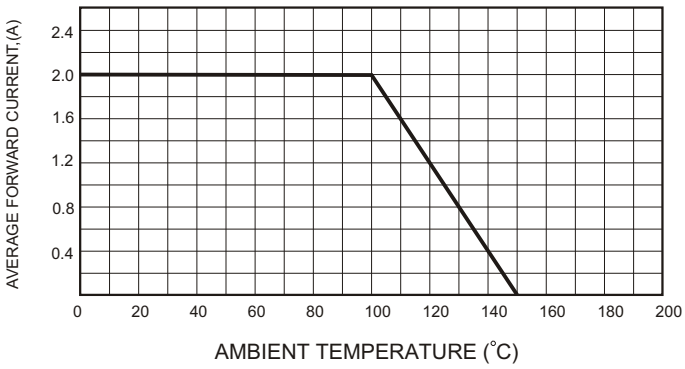


FIG.2-TYPICAL FORWARD CHARACTERISTICS

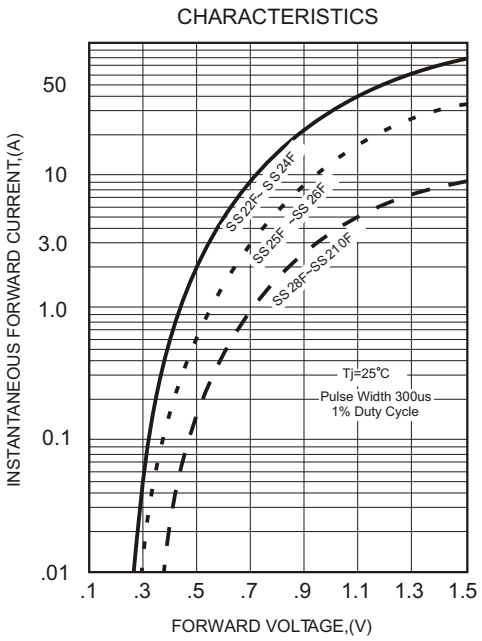


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

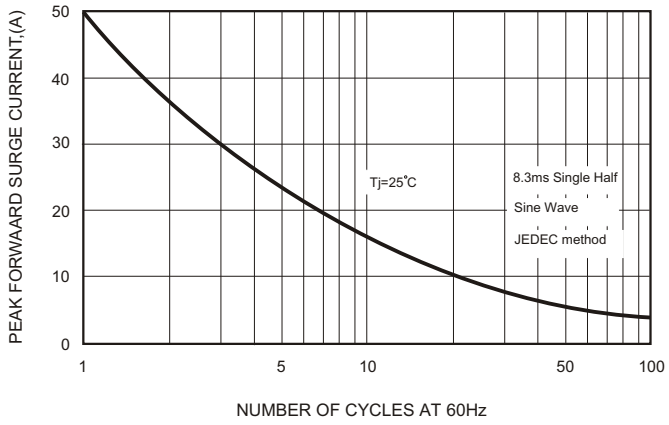


FIG.4-TYPICAL JUNCTION CAPACITANCE

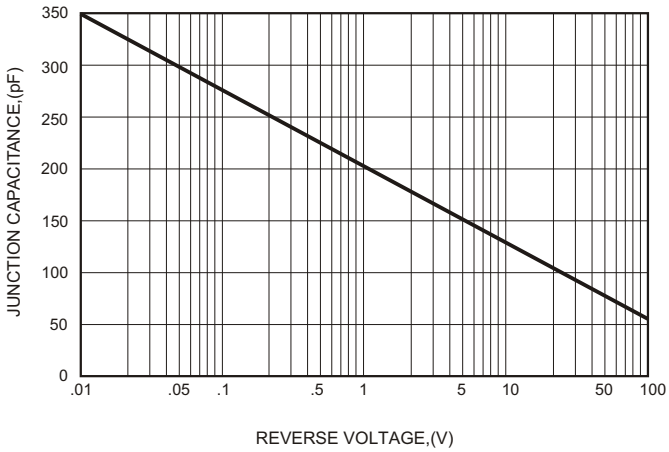
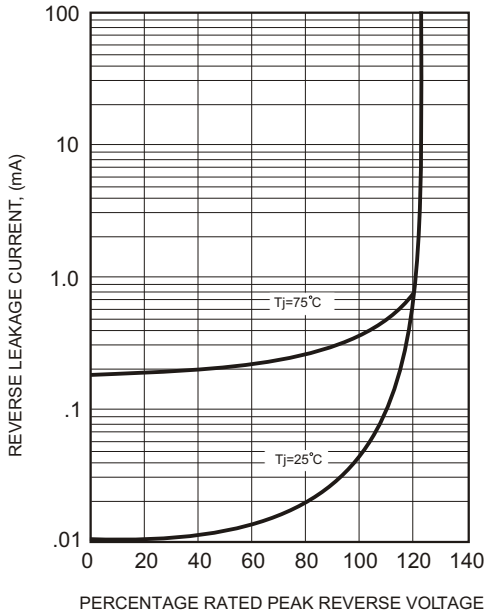
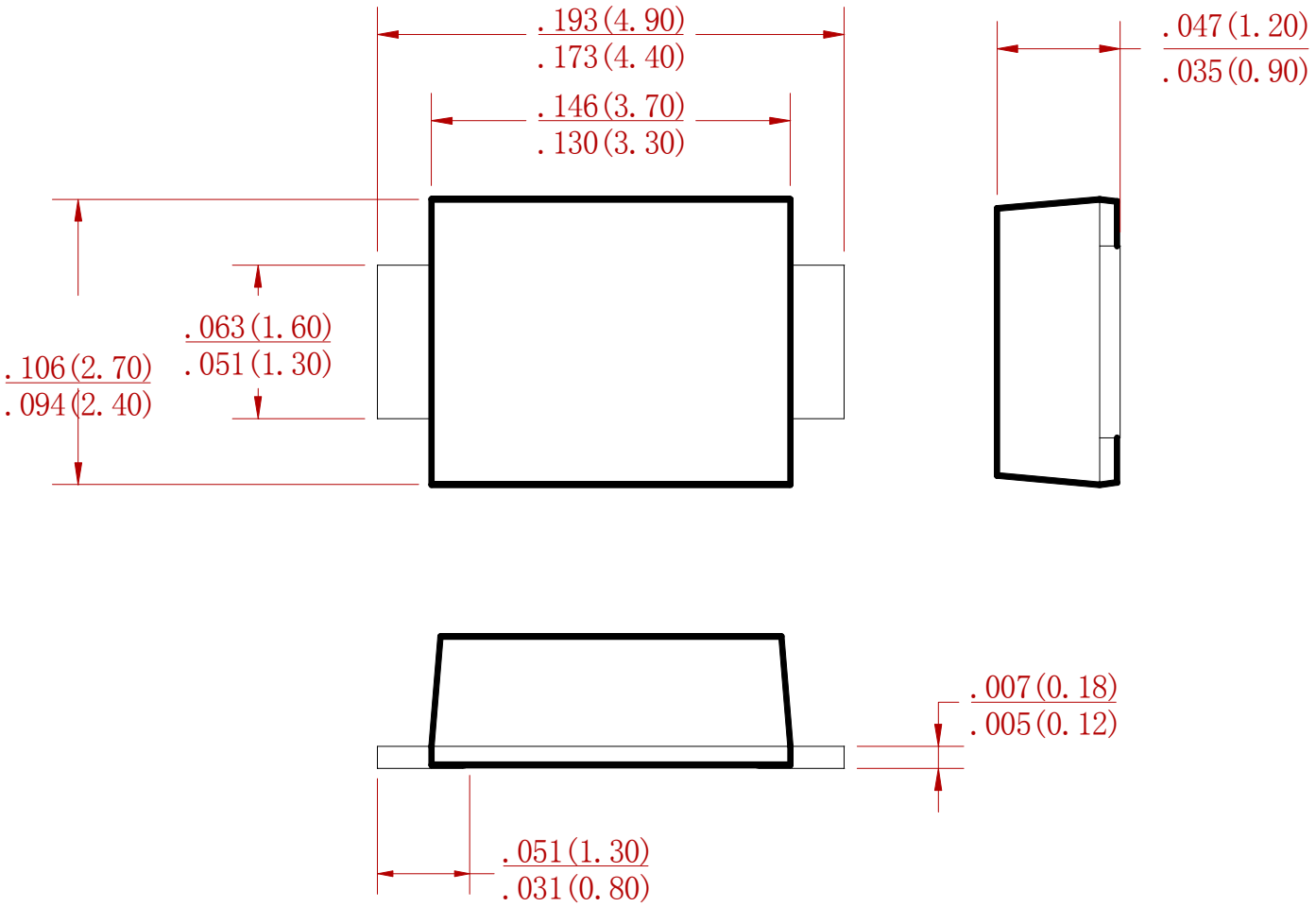


FIG.5 - TYPICAL REVERSE CHARACTERISTICS



PACKAGE MECHANICAL DATA



Dimensions in inches and (millimeters)

REEL SPECIFICATION

P/N	PKG	QTY
SS22F THRU SS2200F	SMAF	3000

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